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CSD18502Q5B

SLPS320A - NOVEMBER 2012 - REVISED JULY 2015

CSD18502Q5B 40 V N-Channel NexFET™ Power MOSFET

Technical

Documents

Features 1

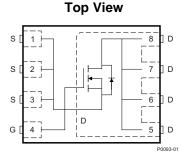
- Ultra-Low Q_a and Q_{ad}
- Low Thermal Resistance
- Avalanche Rated
- Logic Level
- **Pb-Free Terminal Plating**
- **RoHS** Compliant
- Halogen-Free
- SON 5 mm × 6 mm Plastic Package

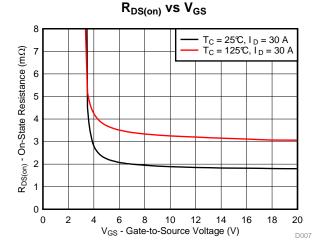
Applications 2

- **DC-DC** Conversion
- Secondary Side Synchronous Rectifier
- Motor Control

3 Description

This 40-V, 1.8-mΩ, 5 mm × 6 mm NexFET[™] power MOSFET is designed to minimize losses in power conversion applications.





Product Summary

T _A = 25°	С	TYPICAL VA	UNIT	
V _{DS}	Drain to source voltage 40			
Qg	Gate charge total (4.5 V)	25		nC
Q _{gd}	Gate charge gate to drain	8.4	nC	
D	Drain to source on resistance	V _{GS} = 4.5 V 2.5		mΩ
R _{DS(on)}	Drain to source on resistance	V _{GS} = 10 V	1.8	mΩ
V _{GS(th)}	Threshold voltage	1.8	V	

Ordering Information⁽¹⁾

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD18502Q5B	2500	13-Inch Reel	SON 5 mm × 6 mm	Tape and
CSD18502Q5BT	250	7-Inch Reel	Plastic Package	Reel

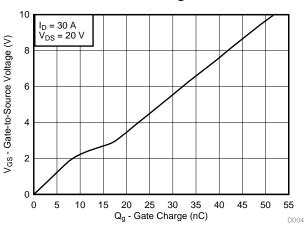
(1) For all available packages, see the orderable addendum at the end of the datasheet.

Absolute Maximum Ratings

T _A = 2	5°C	VALUE	UNIT
V_{DS}	Drain to source voltage	40	V
V_{GS}	Gate to source voltage	±20	V
	Continuous drain current (package limited)	100	
I _D	Continuous drain current (silicon limited), $T_C = 25^{\circ}C$	204	А
	Continuous drain current ⁽¹⁾	26	
I _{DM}	Pulsed drain current ⁽²⁾	400	А
P	Power dissipation ⁽¹⁾	3.2	W
PD	Power dissipation, $T_C = 25^{\circ}C$	156	vv
TJ	Operating junction temperature	-55 to 150	°C
T _{stg}	Storage temperature	-55 to 150	°C
E _{AS}	Avalanche energy, single pulse I_{D} = 88 A, L = 0.1 mH, R_{G} = 25 Ω	387	mJ

(1) Typical $R_{\theta JA}$ = 40°C/W on a 1 inch² , 2 oz. Cu pad on a 0.06 inch thick FR4 PCB.

(2) Max $R_{\theta JC} = 0.8^{\circ}C/W$, pulse duration $\leq 100 \ \mu s$, duty cycle $\leq 1\%$



Gate Charge

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Original (November 2012) to Revision A

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5 Specifications

5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
STATIC	CHARACTERISTICS				
BV_{DSS}	Drain to source voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	40		V
I _{DSS}	Drain to source leakage current	$V_{GS} = 0 V, V_{DS} = 32 V$		1	μA
I _{GSS}	Gate to source leakage current	$V_{DS} = 0 V, V_{GS} = 20 V$		100	nA
V _{GS(th)}	Gate to source threshold voltage	$V_{DS} = V_{GS}, \ I_D = 250 \ \mu A$	1.5 1.8	2.2	V
C	Drain to course on registeres	$V_{GS} = 4.5 \text{ V}, I_{D} = 30 \text{ A}$	2.5	3.3	mΩ
R _{DS(on)}	Drain to source on resistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	1.8	2.3	mΩ
g _{fs}	Transconductance	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	143		S
DYNAMI	C CHARACTERISTICS				
C _{iss}	Input capacitance		3900	5070	pF
C _{oss}	Output capacitance	$V_{GS} = 0 V, V_{DS} = 20 V, f = 1 MHz$	900	1170	pF
C _{rss}	Reverse transfer capacitance		21	27	pF
R_G	Series gate resistance		1.2	2.4	Ω
Qg	Gate charge total (4.5 V)		25	33	nC
Qg	Gate charge total (10 V)		52	68	nC
Q _{gd}	Gate charge gate to drain	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	8.4		nC
Q _{gs}	Gate charge gate to source		10.3		nC
Q _{g(th)}	Gate charge at V _{th}		6.9		nC
Q _{oss}	Output charge	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	59		nC
t _{d(on)}	Turn on delay time		5.3		ns
t _r	Rise time	V _{DS} = 20 V, V _{GS} = 10 V,	6.8		ns
t _{d(off)}	Turn off delay time	$I_{DS} = 30 \text{ A}, \text{ R}_{G} = 0 \Omega$	23		ns
t _f	Fall time		4		ns
DIODE C	CHARACTERISTICS				
V_{SD}	Diode forward voltage	$I_{SD} = 30 \text{ A}, V_{GS} = 0 \text{ V}$	0.8	1	V
Q _{rr}	Reverse recovery charge	V _{DS} = 20 V, I _F = 30 A,	88		nC
t _{rr}	Reverse recovery time	di/dt = 300 A/µs	44		ns

5.2 Thermal Information

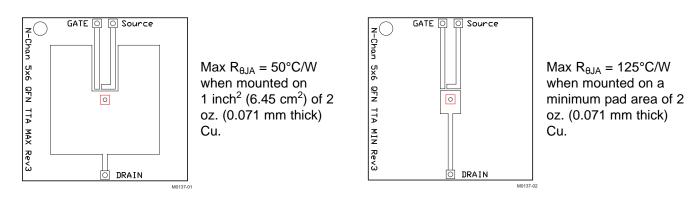
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case (top of package) thermal resistance ⁽¹⁾			0.8	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾⁽²⁾			50	°C/W

 $R_{\theta JC}$ is determined with the device mounted on a 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu pad on a 1.5 inch x 1.5 inch (3.81 cm x 3.81 cm), 0.06 inch (1.52 mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu. (1)

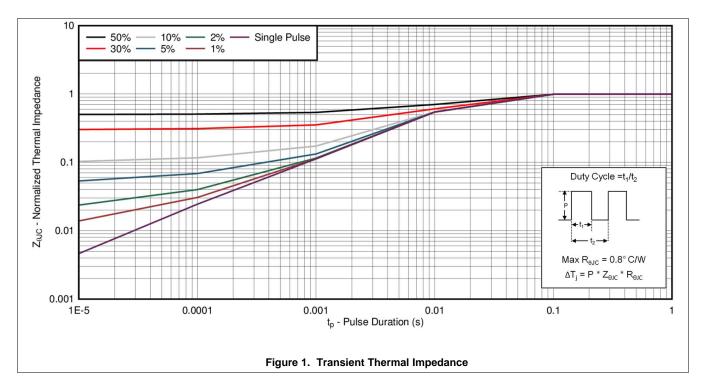
(2)





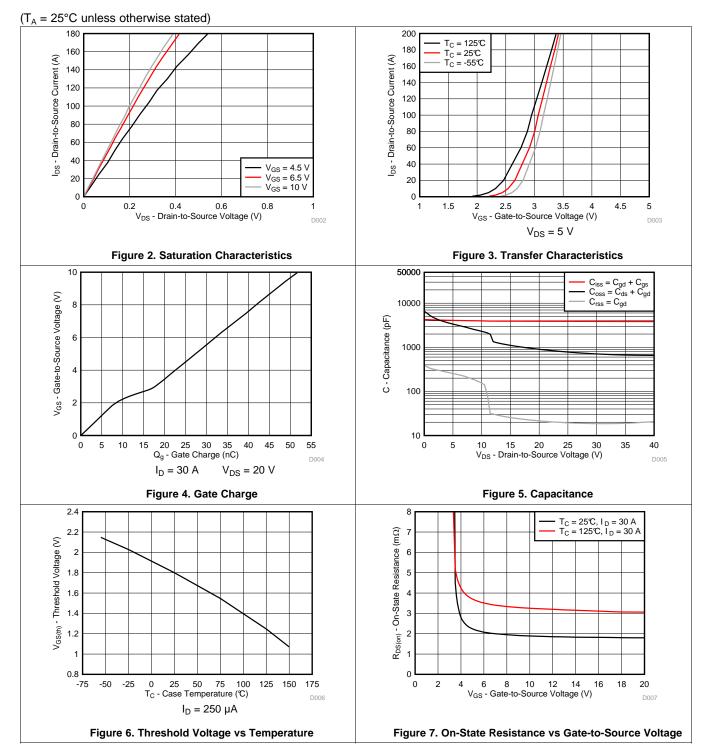
5.3 Typical MOSFET Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$





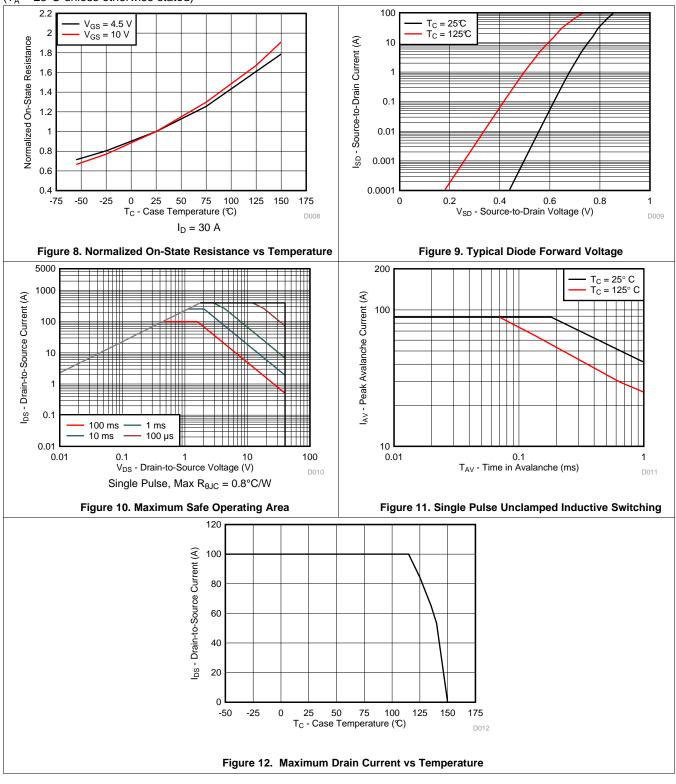
Typical MOSFET Characteristics (continued)





Typical MOSFET Characteristics (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$





6 Device and Documentation Support

6.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E[™] Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.2 Trademarks

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6.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.4 Glossary

SLYZ022 — TI Glossary.

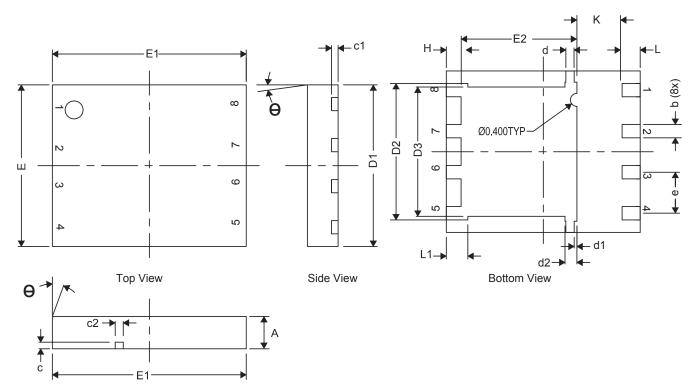
This glossary lists and explains terms, acronyms, and definitions.

CSD18502Q5B SLPS320A – NOVEMBER 2012–REVISED JULY 2015 TEXAS INSTRUMENTS

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7 Mechanical, Packaging, and Orderable Information

7.1 Q5B Package Dimensions

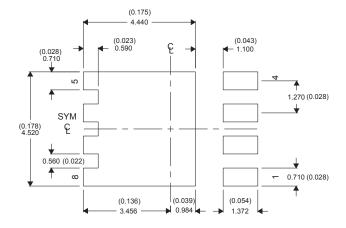


Front View

DIM	MILLIMETERS				
DIM	MIN	NOM	MAX		
А	0.95	1.00	1.05		
b	0.36	0.41	0.46		
С	0.15	0.20	0.25		
c1	0.15	0.20	0.25		
c2	0.20	0.25	0.30		
D1	4.90	5.00	5.10		
D2	4.12	4.22	4.32		
d	0.20	0.25	0.30		
E	4.90	5.00	5.10		
E1	5.90	6.00	6.10		
E2	3.48	3.58	3.68		
е		1.27 TYP			
L	0.46	0.56	0.66		
θ	0°	_	_		
К		1.40 TYP			

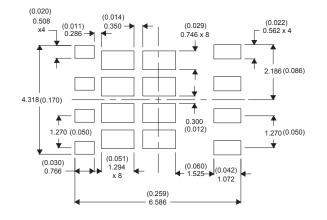


7.2 Recommended PCB Pattern

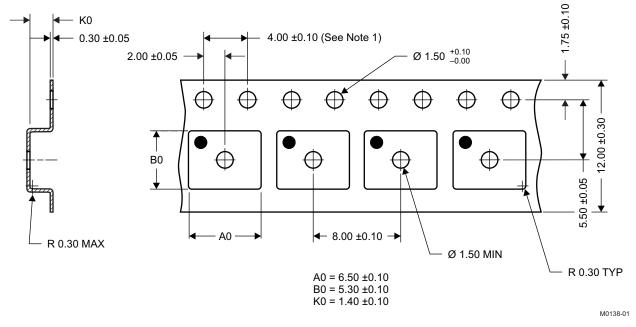


For recommended circuit layout for PCB designs, see *Reducing Ringing Through PCB Layout Techniques* (SLPA005).

7.3 Recommended Stencil Pattern



7.4 Q5B Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket



5-Apr-2016

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD18502Q5B	ACTIVE	VSON-CLIP	DNK	8	2500	Pb-Free (RoHS Exempt)	CU NIPDAU CU SN	Level-1-260C-UNLIM		CSD18502	Samples
CSD18502Q5BT	ACTIVE	VSON-CLIP	DNK	8	250	Pb-Free (RoHS Exempt)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-55 to 150	CSD18502	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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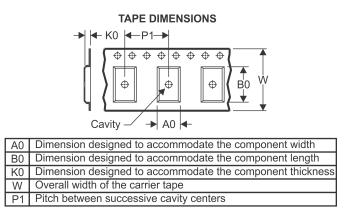
PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD18502Q5B	VSON- CLIP	DNK	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1
CSD18502Q5B	VSON- CLIP	DNK	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1
CSD18502Q5BT	VSON- CLIP	DNK	8	250	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1
CSD18502Q5BT	VSON- CLIP	DNK	8	250	178.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

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PACKAGE MATERIALS INFORMATION

30-Jul-2016



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD18502Q5B	VSON-CLIP	DNK	8	2500	335.0	335.0	32.0
CSD18502Q5B	VSON-CLIP	DNK	8	2500	335.0	335.0	32.0
CSD18502Q5BT	VSON-CLIP	DNK	8	250	335.0	335.0	32.0
CSD18502Q5BT	VSON-CLIP	DNK	8	250	210.0	210.0	52.0

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